

WHAT IS CLAIMED IS:

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1. A semiconductor device comprising:
a semiconductor chip having a circuit
block, a power supply line and a ground line; and
a condenser chip in which a noise
reduction condenser connected to said circuit block
is formed,

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wherein said condenser chip is stacked on
said semiconductor chip.

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2. The semiconductor device as claimed in
claim 1, wherein a plurality of circuit blocks are
formed in said semiconductor chip, and said
condenser chip has a plurality of condensers
corresponding to said circuit blocks.

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3. The semiconductor device as claimed in
claim 1, wherein a plurality of circuit blocks are
formed in said semiconductor chip, and a plurality
of said condenser chips are provided corresponding
to said circuit blocks.

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4. The semiconductor device as claimed in
claims 1, wherein said semiconductor chip has a

first power supply pad provided on a connecting line extending from one of said power supply line and said ground line to said circuit block; and

5 said condenser chip has a second electrode pad connected to the condenser, and the second electrode pad of said condenser chip is electrically connected to the first electrode pad of said semiconductor chip through a bonding wire.

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5. The semiconductor device as claimed in claims 1, wherein said semiconductor chip has a
15 first power supply pad provided on a connecting line extending from one of said power supply line and said ground line to said circuit block; and

 said condenser chip has a second electrode
20 pad connected to the condenser, and said condenser chip is connected to the first electrode pad of said semiconductor chip by flip chip bonding.

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6. The semiconductor device as claimed in claims 1, wherein the noise reduction condenser of said condenser chip is formed by a MOS capacity.

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7. The semiconductor device as claimed in claims 1, wherein said semiconductor chip has a
35 third electrode pad other than said first electrode pad connected to said circuit block;

 said condenser chip has a fourth electrode

pad other than said second electrode pad connected to the condenser; and

an inductor connected to at least one of said power line and said ground line is formed by connecting said fourth electrode pad of said
5 condenser chip and said third electrode pad of said semiconductor chip by a bonding wire.

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8. The semiconductor device as claimed in claim 7, wherein a plurality of said fourth electrode pads of said condenser chip are provided and a plurality of said third electrode pads of said
15 semiconductor chip are provided; and

said inductor is formed by alternately and sequentially connecting said fourth electrode pads of said condenser chip and said third electrode pads
20 of said semiconductor chip by bonding wires.

9. A semiconductor device comprising: a
25 first semiconductor chip having a circuit block, a power supply line and a ground line; and a second semiconductor chip stacked on said first semiconductor chip, wherein said first semiconductor chip has a first electrode pad separated from a
30 circuit formed within said first semiconductor chip;

said second semiconductor chip has a second electrode pad separated from a circuit formed within said second semiconductor chip; and

an inductor connected to at least one of
35 said power line and said ground line is formed by connecting said first electrode pad of said first semiconductor chip and said second electrode pad of

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said second semiconductor chip by a bonding wire.

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10. The semiconductor device as claimed in claim 9, wherein a plurality of said first electrode pads of said first semiconductor chip are provided and a plurality of said second electrode pads of

10 said second semiconductor chip are provided; and

said inductor is formed by alternately and sequentially connecting said first electrode pads of said first semiconductor chip and said second electrode pads of said second semiconductor chip by

15 bonding wires.

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